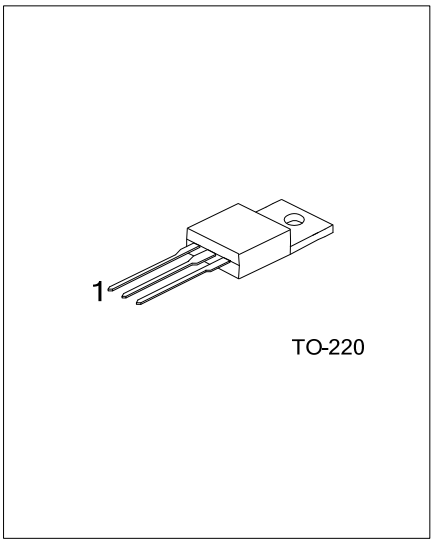
2SA940

PNP SILICON TRANSISTOR

PNP SILICON POWER TRANSISTORS



■ FEATURES

* Collector-Emitter Voltage: V_{CEO}=-150V (Min.)
* DC Current Gain: h_{FE}=40~140 @ I_C=-500mA
* Complementary of NPN 2SC2073

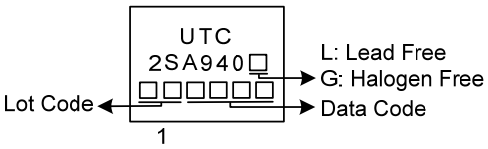
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SA940L- TA3-T	2SA940G-TA3-T	TO-220	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

2SA940G-TA3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) TA3: TO-220 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector- Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Best Current	I_B	-0.5	A
Collector Current Continuous	I_C	-1.5	A
Collector Current Peak	I_{CM}	-3.0	A
Collector Dissipation	P_C	25	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction-to-Case	θ_{JC}	5.0	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	I_C =-1.0mA, I_B =0	-150			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C =-5.0mA, I_B =0	-150			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_B =-1.0mA, I_C =0	-5.0			V
Collect Cut-off Current	I_{CBO}	V_{CB} =-120V, I_E =0			-10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} =-5.0V, I_C =0			-10	μA
ON CHARACTERISTICS						
DC Current Ratio	h_{FE}	V_{CE} =-10V, I_C =-0.5A	40		140	
Base-Emitter on Voltage	$V_{BE(ON)}$	V_{CE} =-5.0V, I_C =-500mA	-0.65		-0.85	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C =-0.5A, I_B =-50mA			-1.5	V
Current Gain Bandwidth Product	f_T	V_{CE} =-10V, I_C =-0.5A, f =1MHz	4.0			MH_Z